

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
20V	42mΩ @ V _{GS} = 10V	3.5A
	45mΩ @ V _{GS} = 4.5V	3.3A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

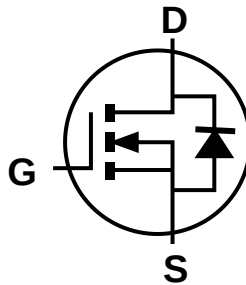
Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 0.006 grams (Approximate)

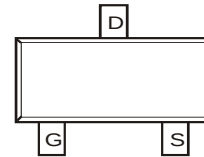
SOT323



Top View



Equivalent Circuit



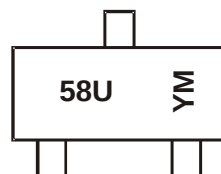
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2058UW-7	SOT323	3000/Tape & Reel
DMN2058UW-13	SOT323	10000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



58U= Product Type Marking Code
 YM or YM = Date Code Marking for SAT
 Y or Y = Year (ex: F = 2018)
 M = Month (ex: 9 = September)

Date Code Key

Year Code	2017	2018	2019	2020	2021	2022	2023	2024	2025
	E	F	G	H	I	J	K	L	M

Month Code	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	3.5 3.0	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)			I _{DM}	20	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.5	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	259	°C/W
Total Power Dissipation (Note 6)			P _D	0.7	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	175	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.4	—	1.2	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	31.5	42	mΩ	V _{GS} = 10V, I _D = 3A
			32	45		V _{GS} = 4.5V, I _D = 2A
			40.5	60		V _{GS} = 2.5V, I _D = 2A
			48	91		V _{GS} = 1.8V, I _D = 1A
Diode Forward Voltage	V _{SD}	—	0.78	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	281	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	50	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	39	—	pF	
Gate Resistance	R _g	—	3.1	—	Ω	f = 1.0MHz, V _{GS} = 0V, V _{DS} = 0V
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	3.6	—	nC	V _{DS} = 10V, I _D = 6.0A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	7.7	—	nC	
Gate-Source Charge	Q _{gs}	—	0.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	2.0	—	ns	V _{GS} = 4.5V, V _{DD} = 10V, R _g = 6Ω, I _D = 6.0A
Turn-On Rise Time	t _r	—	4.9	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	9.9	—	ns	
Turn-Off Fall Time	t _f	—	3.3	—	ns	
Body Diode Reverse Recovery Time	t _{RR}	—	5.4	—	ns	I _F = 6.0A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	0.7	—	nC	I _F = 6.0A, di/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

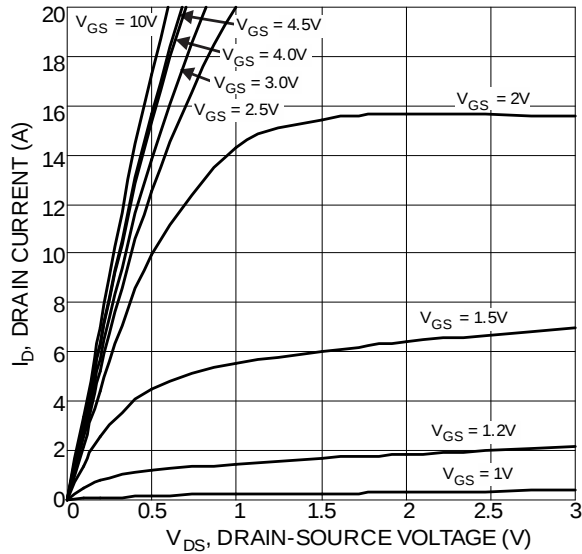


Figure 1 Typical Output Characteristic

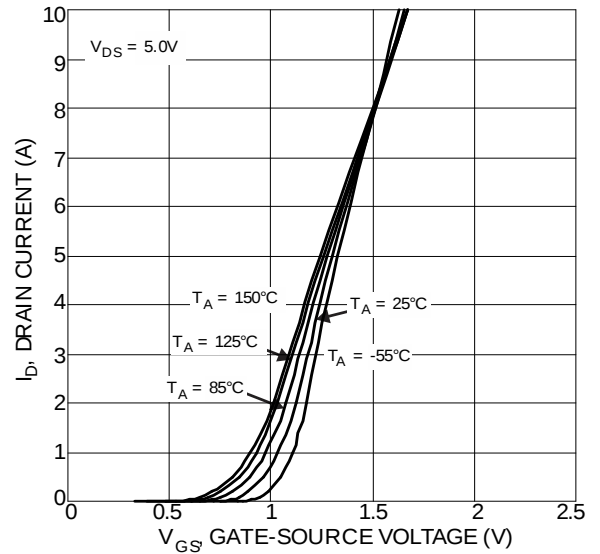


Figure 2 Typical Transfer Characteristics

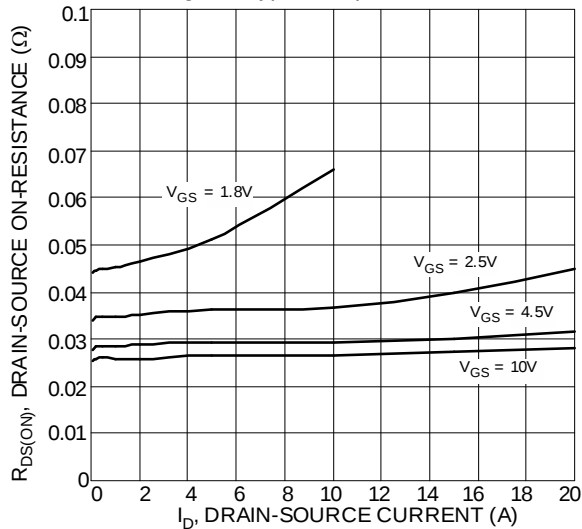


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

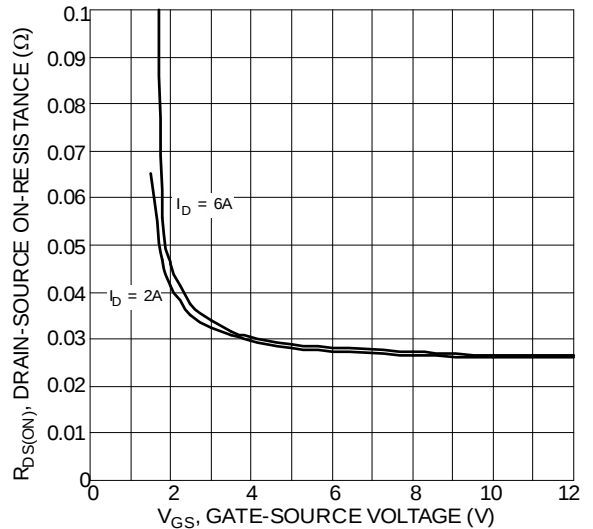


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

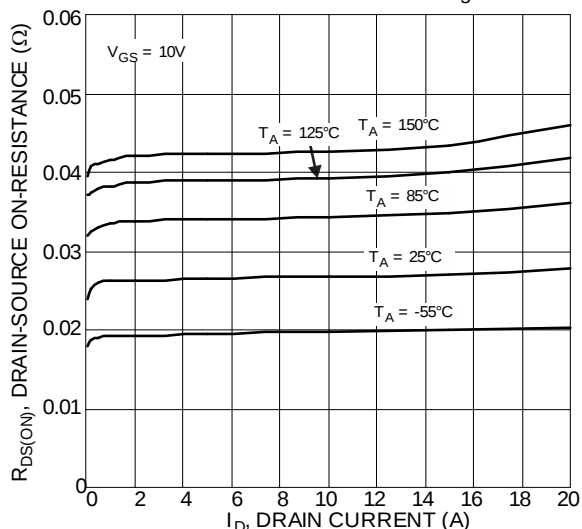


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

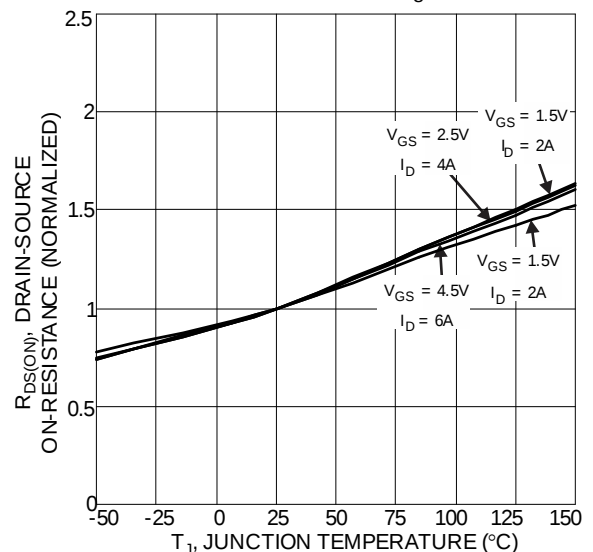


Figure 6 On-Resistance Variation with Temperature

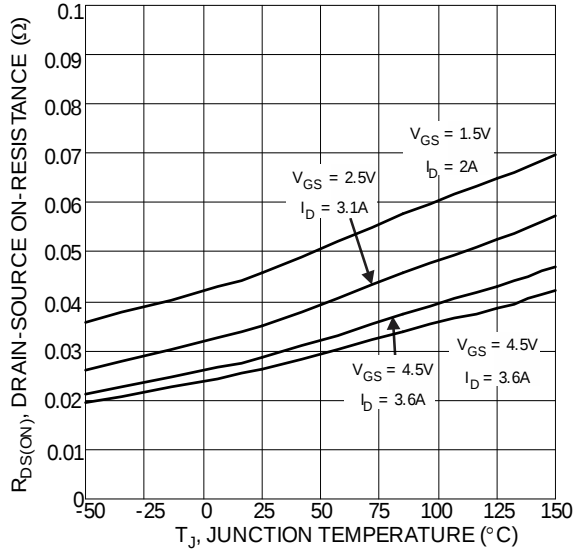


Figure 7 On-Resistance Variation with Temperature

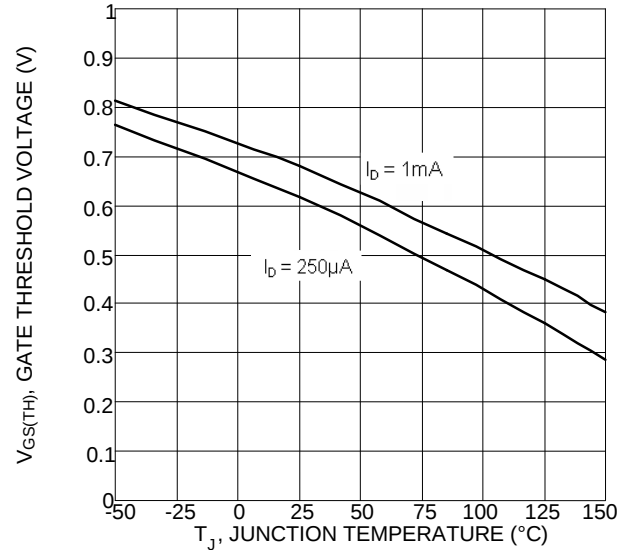


Figure 8 Gate Threshold Variation vs. Junction Temperature

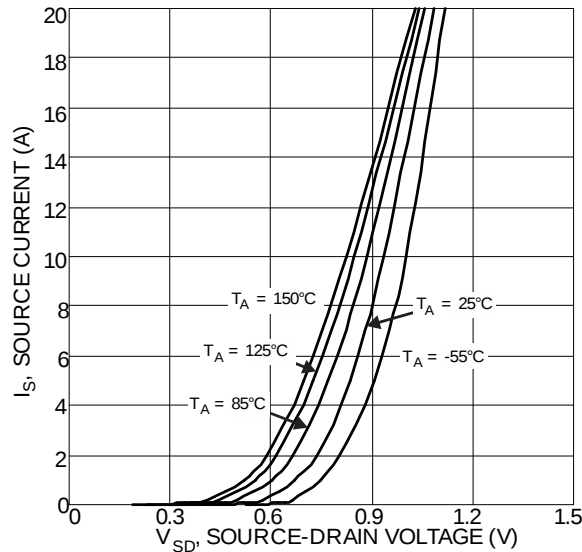


Figure 9 Diode Forward Voltage vs. Current

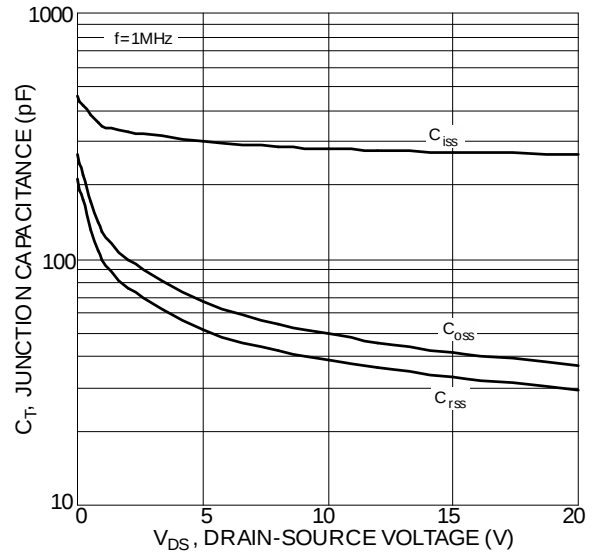


Figure 10 Typical Junction Capacitance

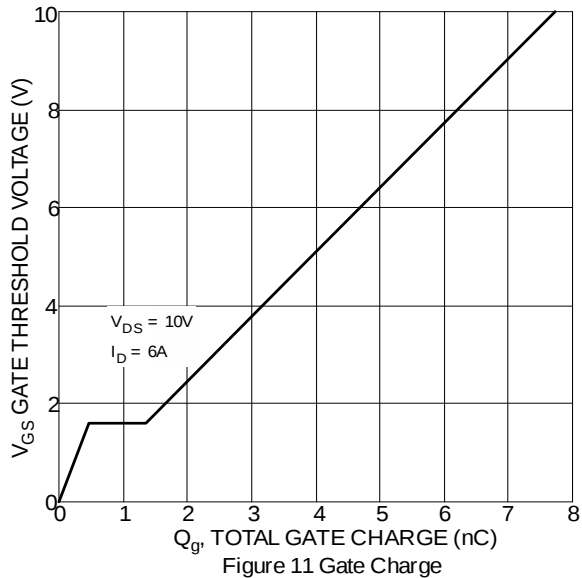


Figure 11 Gate Charge

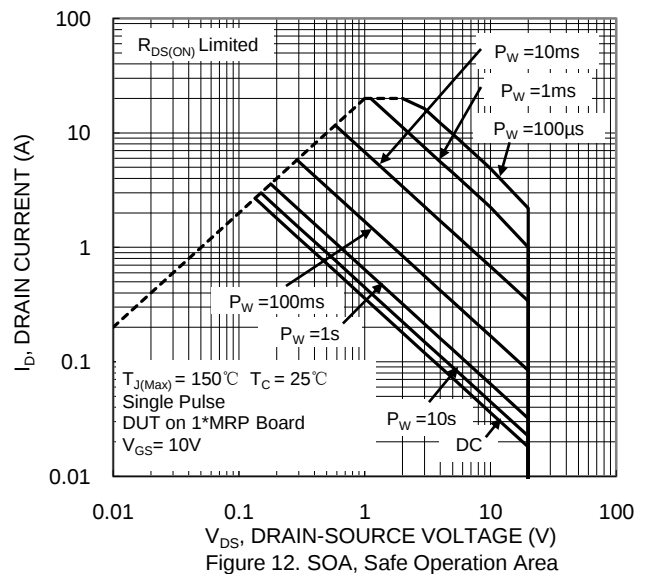


Figure 12. SOA, Safe Operation Area

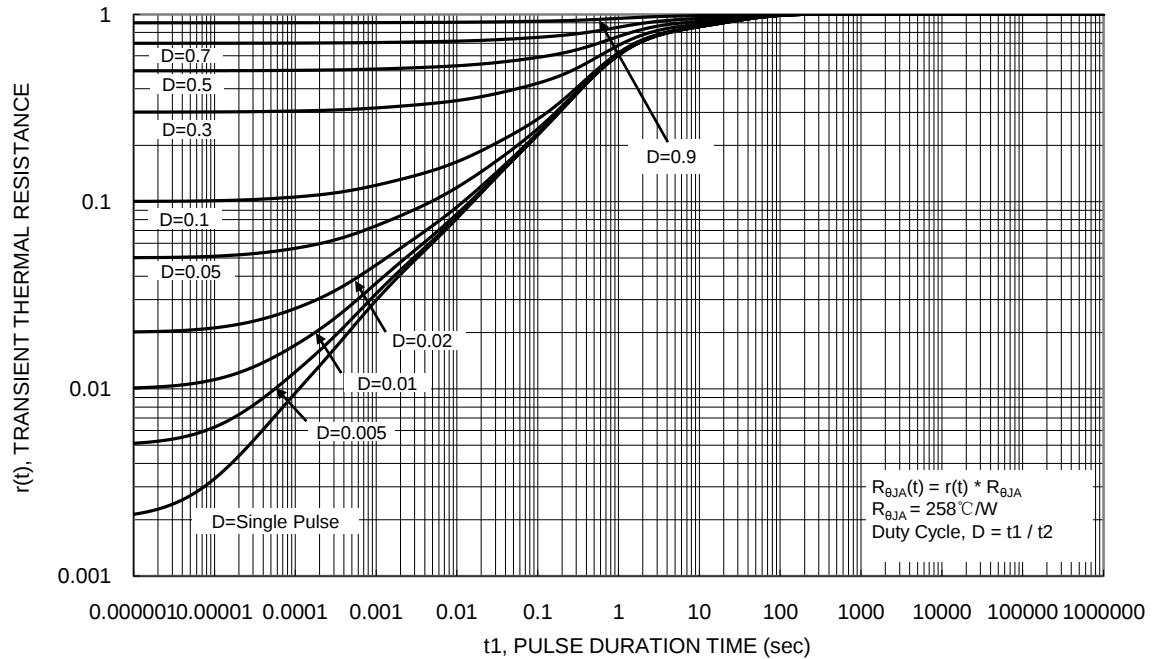
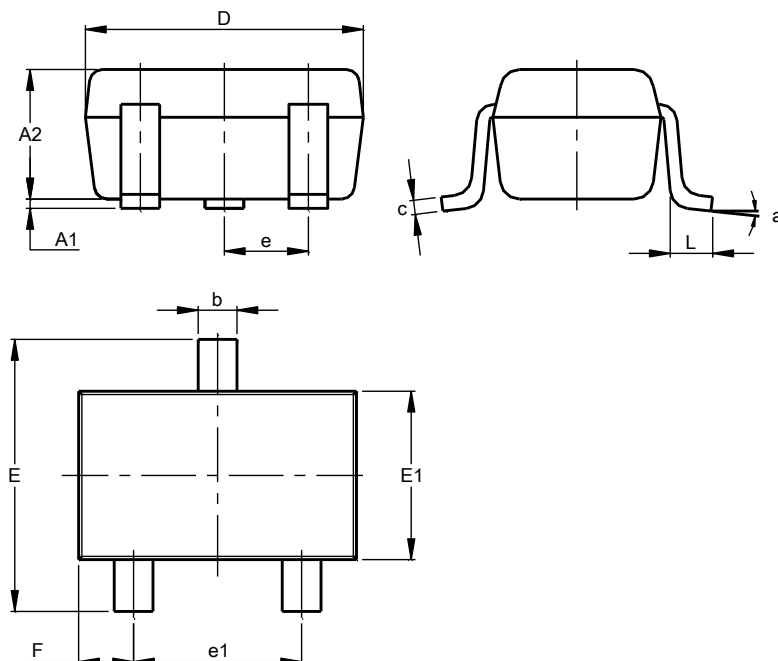


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323

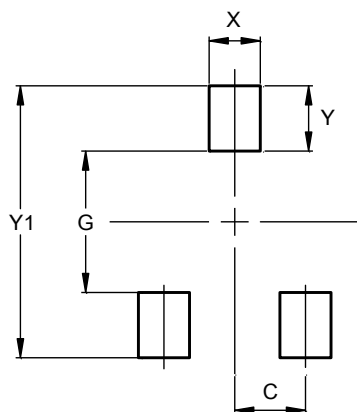


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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